

Technical Data

DIODE



maximum ratings

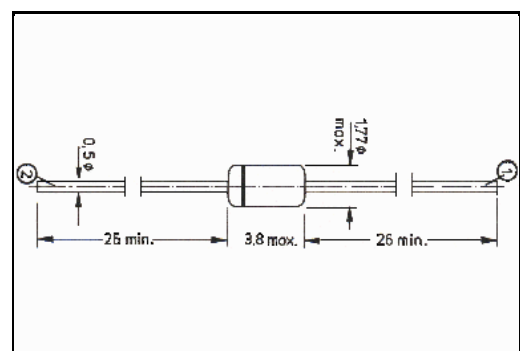
Voltage, Reverse (VR)	125.0	V	NO.	1N3595
Voltage, Reverse Peak (VRM)	150.0	V	TYPE	SILICON
Current at VR = 0V (IO)		A		
Current Average Rectified (IF)	0.2	A		
Current Surge Peak (IFM)	0.6	A	CASE	DO-35
Current, Surge (IFM) at tp = 1 μs	4.0	A		
Max. Power Dissipation (PT) at TA = 25° C	0.5	W		
Max. Thermal Resistance (Rth J-A)	300.0	°C/W		
Max. Junction Temperature (TJ)	175.0	°C		

PERFORMANCE CHARACTERISTICS at T_c = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VRM	IR = 100.0 μA (1)	150.0	-	V
2.	IR	VR = 125.0 V	-	1.0	nA
3.	IR	VR = 125.0 V, TA = 150.0° C	-	3.0	μA
4.	VF	IF = 1.0 mA (1)	0.52	0.68	V
5.	VF	IF = 5.0 mA (1)	0.6	0.75	V
6.	VF	IF = 10.0 mA (1)	0.65	0.8	V
7.	VF	IF = 50.0 mA (1)	0.74	0.88	V
8.	VF	IF = 100.0 mA (1)	0.79	0.92	V
9.	VF	IF = 200.0 mA (1)	0.83	1.0	V
10.	CT	VR = 0 V, f = 1.0 MHz	-	8.0	pF
11.	trr	IF = 10.0 mA, VR = 35.0 V	-	3.0	ns
12.					
13.					
14.					
15.					
16.					
17.					
18.					
19.					
20.					

Notes (1)pulse-tested tp ≤ 300 μs, duty cycle ≤ 2 %

DIMENSIONS
in mm



Marking 3595
Customer GENERAL PURPOSE